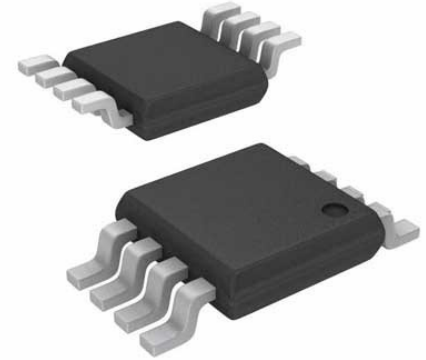


High Isolation, Nonreflective, GaAs, SPDT Switch, 100 MHz to 4 GHz

Manufacturers	Analog Devices, Inc
Package/Case	MSOP-8
Product Type	RF Switches ; SPST, SPDT, SP3T, SP4T, SP5T, SP6T, SP8T
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for HMC349AMS8G or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

The HMC349AMS8G is a gallium arsenide (GaAs), pseudo-morphic high electron mobility transistor (PHEMT), single-pole, double throw (SPDT) switch specified from 100 MHz to 4 GHz.

The HMC349AMS8G is well suited for cellular infrastructure applications by yielding high isolation of 57 dB, low insertion loss of 0.9 dB, high input IP3 of 52 dBm, and high input P1dB of 34 dBm.

The HMC349AMS8G operates with a single positive supply voltage from 3 V to 5 V and provides a CMOS-/TTL-compatible control interface.

The HMC349AMS8G comes in an 8-lead mini small outline package with an exposed pad.

Features

Nonreflective, 50 Ω design

High isolation: 57 dB to 2 GHz

Low insertion loss: 0.9 dB to 2 GHz

High input linearity

1 dB power compression (P1dB): 34 dBm typical

Third-order intercept (IP3): 52 dBm typical

High power handling

33.5 dBm through path

26.5 dBm terminated path

Single positive supply: 3 V to 5 V

CMOS-/TTL-compatible control

All off state control

8-lead mini small outline package with exposed pad (MINI_SO_EP)

Application

Cellular/4G infrastructure

Wireless infrastructure

Mobile radios

Test equipment

Related Products



[HMC3653LP3BE](#)

Analog Devices, Inc
QFN-12



[HMC253AQS24](#)

Analog Devices, Inc
24-SSOP (0.154, 3.90mm Width)



[HMC358MS8GE](#)

Analog Devices, Inc
MSOP-8



[HMC453ST89E](#)

Analog Devices, Inc
ST89E



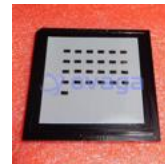
[HMC441LP3E](#)

Analog Devices, Inc
QFN-16



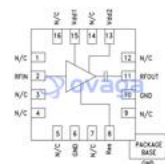
[HMC948LP3E](#)

Analog Devices, Inc
LP3



[HMC490](#)

Analog Devices, Inc
SMD



[HMC618ALP3E](#)

Analog Devices, Inc
QFN-16